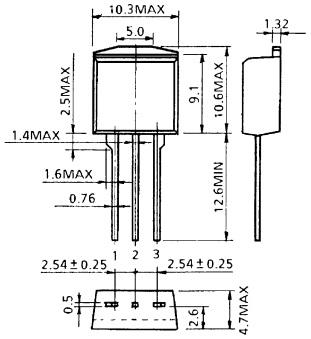
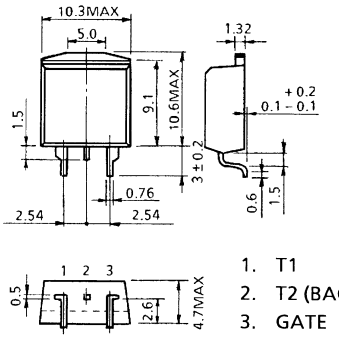
TOSHIBA BIDIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM6G48, USM6G48, SM6J48, USM6J48
SM6G48A, USM6G48A, SM6J48A, USM6J48A

AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off−State Voltage : V_{DRM} = 400V, 600V
- R.M.S On−State Current : $I_{T\ (RMS)}$ = 6A
- Gate Trigger Current
  : I_{GT} = 30mA Max.
  : I_{GT} = 20mA Max. (“A” Type)

Unit: mm

SM6G48, SM6J48, SM6G48A, SM6J48A	USM6G48, USM6J48, USM6G48A, USM6J48A
 1. T1 2. T2 3. GATE	 1. T1 2. T2 (BACK SIDE) 3. GATE
JEDEC —	JEDEC —
JEITA —	JEITA —
TOSHIBA 13−10J1A	TOSHIBA 13−10J2A

Weight: 1.7g

MAXIMUM RATINGS

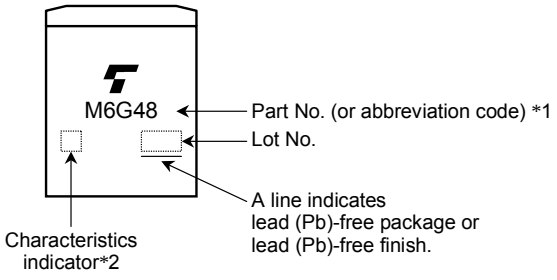
CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off−State Voltage	(U)SM6G48 (U)SM6G48A	V_{DRM}	400	V
	(U)SM6J48 (U)SM6J48A		600	
R.M.S On−State Current		$I_{T\ (RMS)}$	6	A
Peak One Cycle Surge On−State Current (Non-Repetitive)		I_{TSM}	60 (50Hz)	A
			66 (60Hz)	
I^2t Limit Value		I^2t	18	A^2s
Critical Rate of Rise of On−State Current (Note 1)		di / dt	50	A / μs
Peak Gate Power Dissipation		P_{GM}	5	W
Average Gate Power Dissipation		$P_{G\ (AV)}$	0.5	W
Peak Forward Gate Voltage		V_{GM}	10	V
Peak Forward Gate Current		I_{GM}	2	A
Junction Temperature		T_j	−40~125	°C
Storage Temperature Range		T_{stg}	−40~125	°C

Note 1: V_{DRM}=0.5×Rated
$I_{TM} \leq 9A$
$t_{gw} \geq 10\mu s$
$t_{gr} \leq 250ns$
$i_{gp} = I_{GT} \times 2.0$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

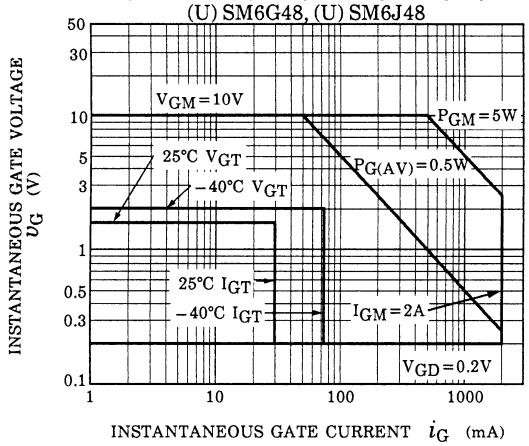
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off−State Current			I_{DRM}	V_{DRM} = Rated		—	—	20	μA
Gate Trigger Voltage		I	V_{GT}	V_D = 12V, R_L = 20Ω	T2 (+), Gate (+)	—	—	1.5	V
		II			T2 (+), Gate (−)	—	—	1.5	
		III			T2 (−), Gate (−)	—	—	1.5	
		IV			T2 (−), Gate (+)	—	—	—	
Gate Trigger Current	(U)SM6G48 (U)SM6J48	I	I_{GT}	V_D = 12V, R_L = 20Ω	T2 (+), Gate (+)	—	—	30	mA
		II			T2 (+), Gate (−)	—	—	30	
		III			T2 (−), Gate (−)	—	—	30	
		IV			T2 (−), Gate (+)	—	—	—	
	(U)SM6G48A (U)SM6J48A	I			T2 (+), Gate (+)	—	—	20	
		II			T2 (+), Gate (−)	—	—	20	
		III			T2 (−), Gate (−)	—	—	20	
		IV			T2 (−), Gate (+)	—	—	—	
Peak On−State Voltage			V_{TM}	I_{TM} = 9A		—	—	1.5	V
Gate Non−Trigger Voltage			V_{GD}	V_D = Rated, Tc = 125°C		0.2	—	—	V
Holding Current			I_H	V_D = 12V, I_{TM} = 1A		—	—	50	mA
Thermal Resistance			$R_{th\ (j-c)}$	Junction to Case, AC		—	—	3.2	°C / W
Critical Rate of Rise of Off−State Voltage	(U)SM6G48 (U)SM6J48		dv / dt	V_{DRM} = Rated, T_j = 125°C Exponential Rise		—	300	—	V / μs
	(U)SM6G48A (U)SM6J48A					—	200	—	
Critical Rate of Rise of Off−State Voltage at Commutation	(U)SM6G48 (U)SM6J48		(dv / dt) c	V_{DRM} = 400V, T_j = 125°C (di / dt) c = −3.3A / ms		10	—	—	V / μs
	(U)SM6G48A (U)SM6J48A					4	—	—	

MARKING

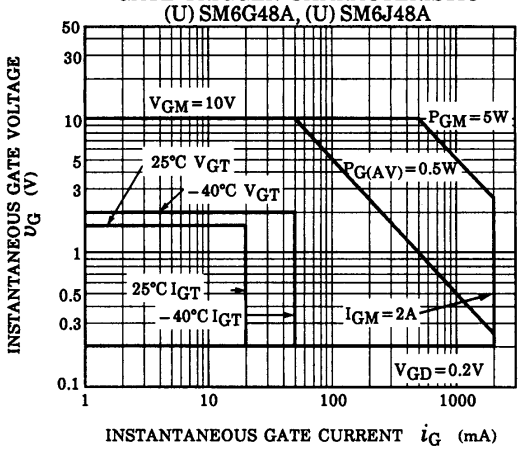


	Part No. (or abbreviation code)	Part No.
*1	M6G48	SM6G48, SM6G48A
		USM6G48, USM6G48A
	M6J48	SM6J48, SM6J48A
		USM6J48, USM6J48A
*2	Nothing	SM6G48, SM6J48
		USM6G48, USM6J48
	A	SM6G48A,SM6J48A
		USM6G48A, USM6J48A

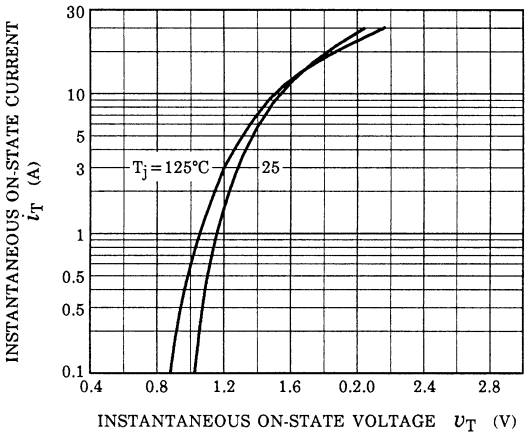
GATE TRIGGER CHARACTERISTIC
(U) SM6G48, (U) SM6J48



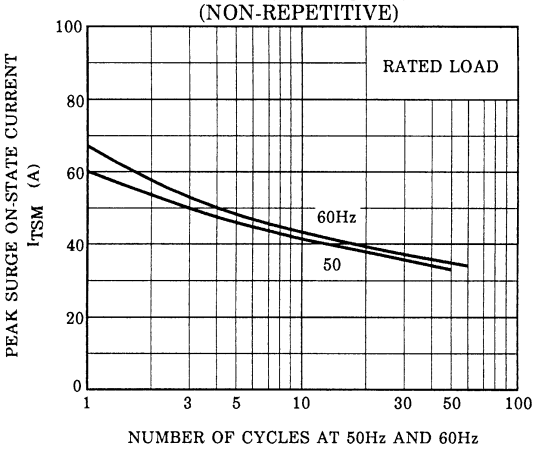
GATE TRIGGER CHARACTERISTIC
(U) SM6G48A, (U) SM6J48A



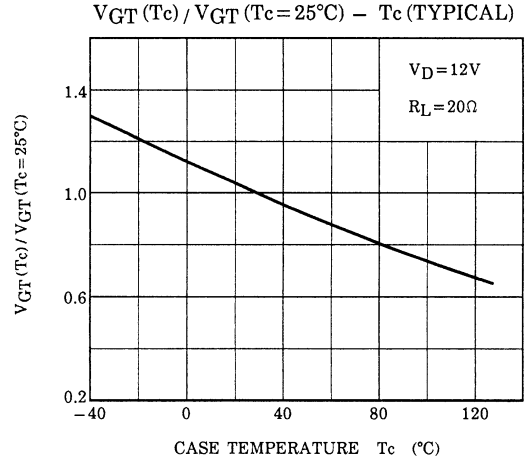
$i_T - v_T$



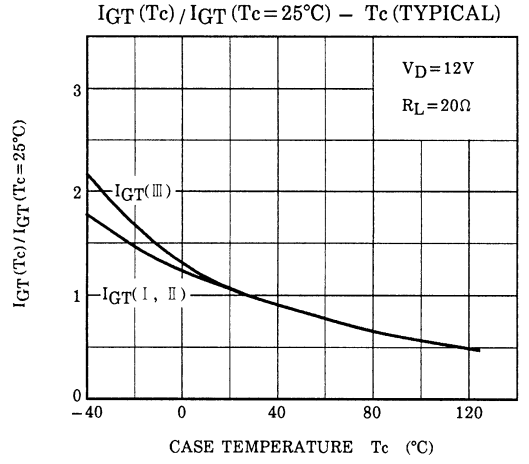
SURGE ON-STATE CURRENT
(NON-REPETITIVE)



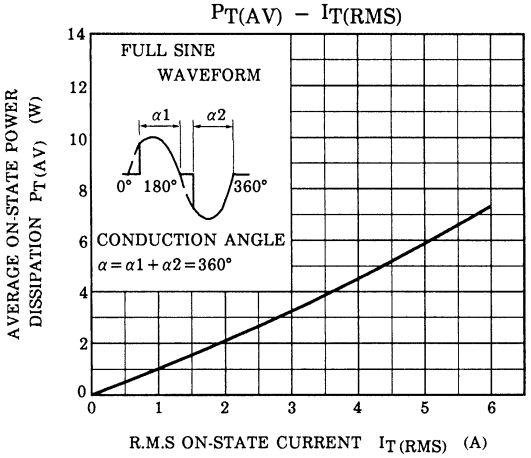
V_{GT} (Tc) / V_{GT} (Tc = 25°C) − Tc (TYPICAL)



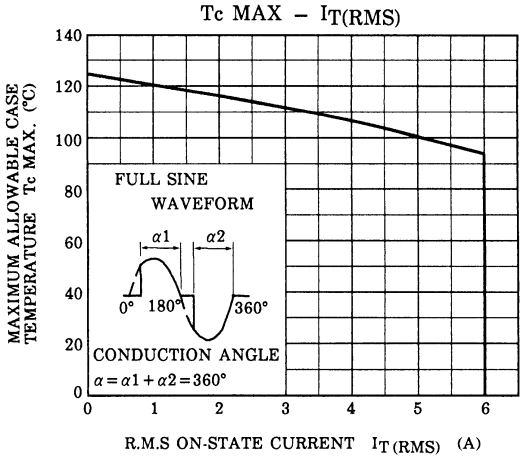
I_{GT} (Tc) / I_{GT} (Tc = 25°C) − Tc (TYPICAL)



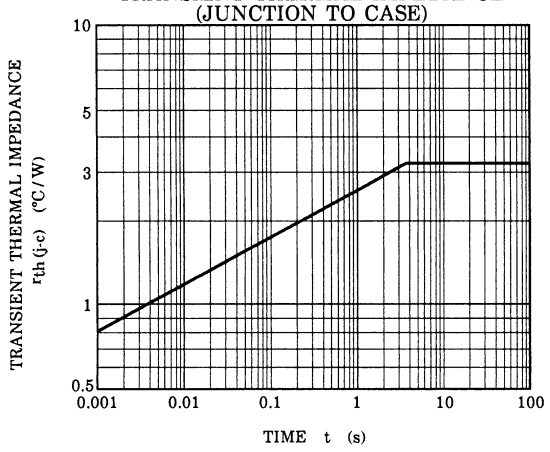
$P_{T(AV)}$ – $I_{T(RMS)}$



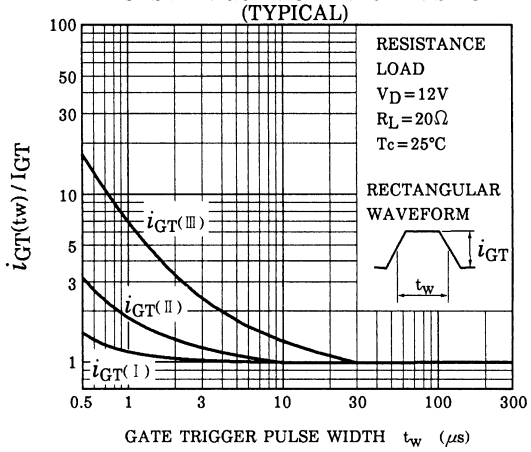
Tc MAX – $I_{T(RMS)}$



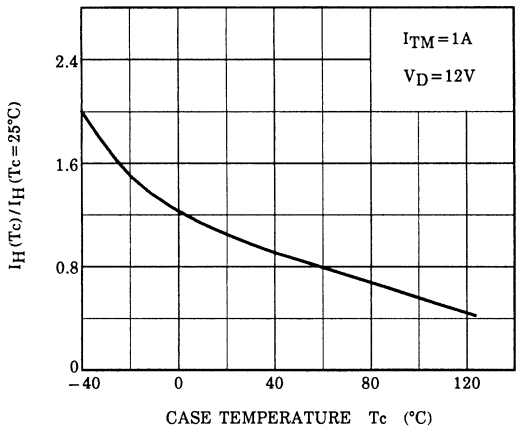
TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



PULSE TRIGGER CHARACTERISTIC (TYPICAL)



$I_H(Tc) / I_H(Tc=25°C)$ – Tc (TYPICAL)



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